

Features

- 600-Volt Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

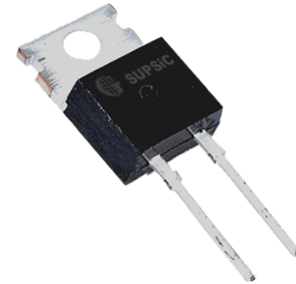
- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

Part Number	Package
GC3D02060A	TO-220-2

V_{RRM}	=	600 V
$I_F (T_c=135^\circ\text{C})$	=	4 A
Q_c	=	5.8 nC



TO-220-2

Package



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	600	V		
V_{RSM}	Surge Peak Reverse Voltage	600	V		
V_{DC}	DC Blocking Voltage	600	V		
I_F	Continuous Forward Current	8 4 2	A	$T_c=25^\circ\text{C}$ $T_c=135^\circ\text{C}$ $T_c=161^\circ\text{C}$	Fig. 3
I_{FRM}	Repetitive Peak Forward Surge Current	11 7.5	A	$T_c=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	16.5 15	A	$T_c=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_c=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	Fig. 8
I_{FSM}	Non-Repetitive Peak Forward Surge Current	120 110	A	$T_c=25^\circ\text{C}$, $t_p=10$ μs , Pulse $T_c=110^\circ\text{C}$, $t_p=10$ μs , Pulse	Fig. 8
P_{tot}	Power Dissipation	39.5 17	W	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	$V_R=0-600\text{V}$	
$\int i^2 dt$	i^2t value	1.35 1.12	A ² s	$T_c=25^\circ\text{C}$, $t_p=10$ ms $T_c=110^\circ\text{C}$, $t_p=10$ ms	
T_j, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 1.8	1.7 2.4	V	$I_F = 2\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 2\text{ A}$ $T_J = 175^\circ\text{C}$	Fig.1
I_R	Reverse Current	3 6	15 55	μA	$V_R = 600\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 600\text{ V}$ $T_J = 175^\circ\text{C}$	Fig. 2
Q_C	Total Capacitive Charge	5.8		nC	$V_R = 400\text{ V}$, $I_F = 2\text{ A}$ $di/dt = 500\text{ A}/\mu\text{S}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	175 10.5 8.5		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 200\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	Fig. 6
E_C	Capacitance Stored Energy	0.8		μJ	$V_R = 400\text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	TO-220 Package Thermal Resistance from Junction to Case	3.8	$^\circ\text{C}/\text{W}$

Typical Performance

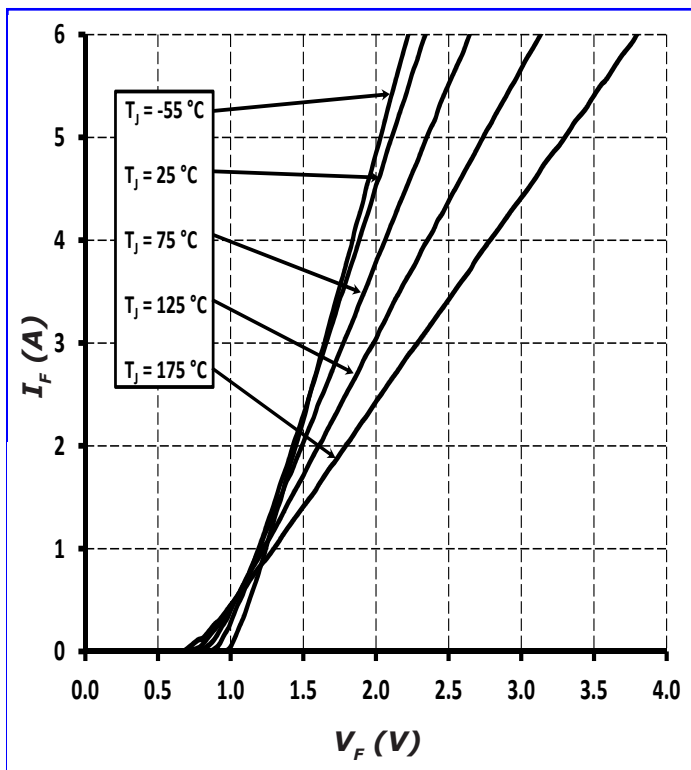


Figure 1. Forward Characteristics

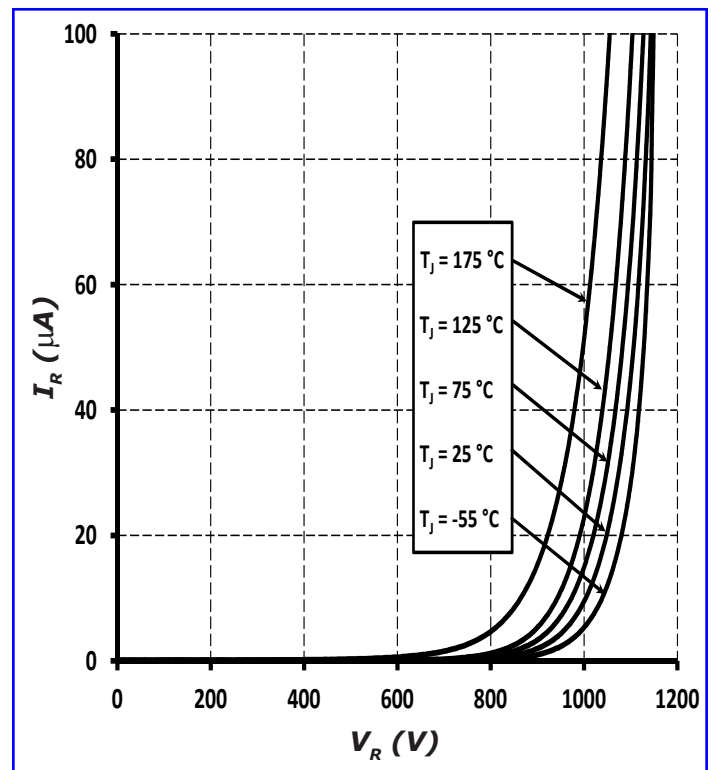


Figure 2. Reverse Characteristics

Typical Performance

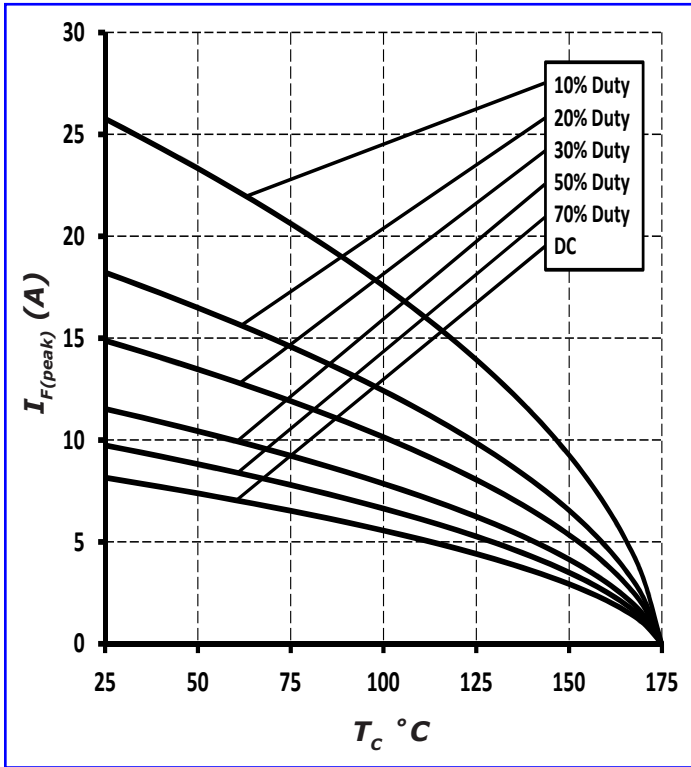


Figure 3. Current Derating

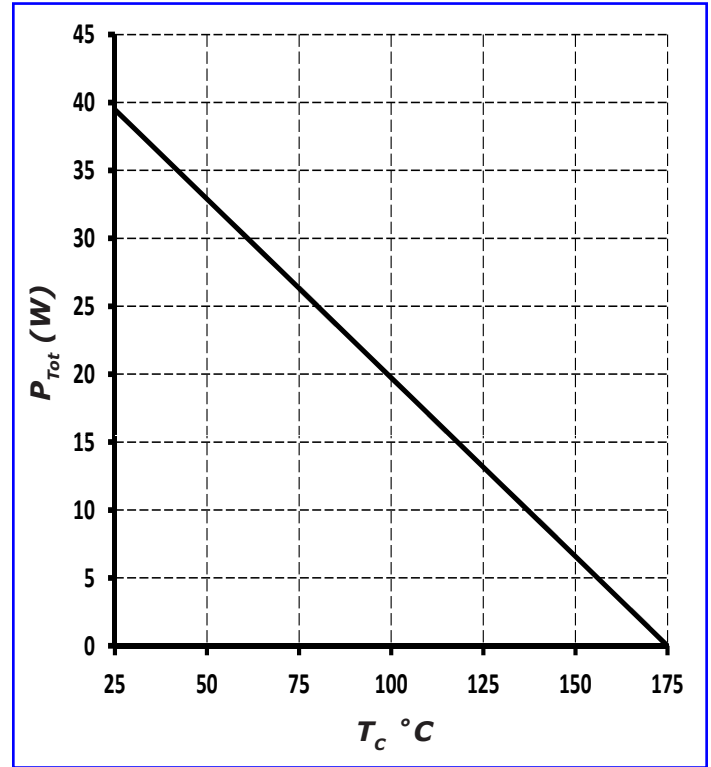


Figure 4. Power Derating

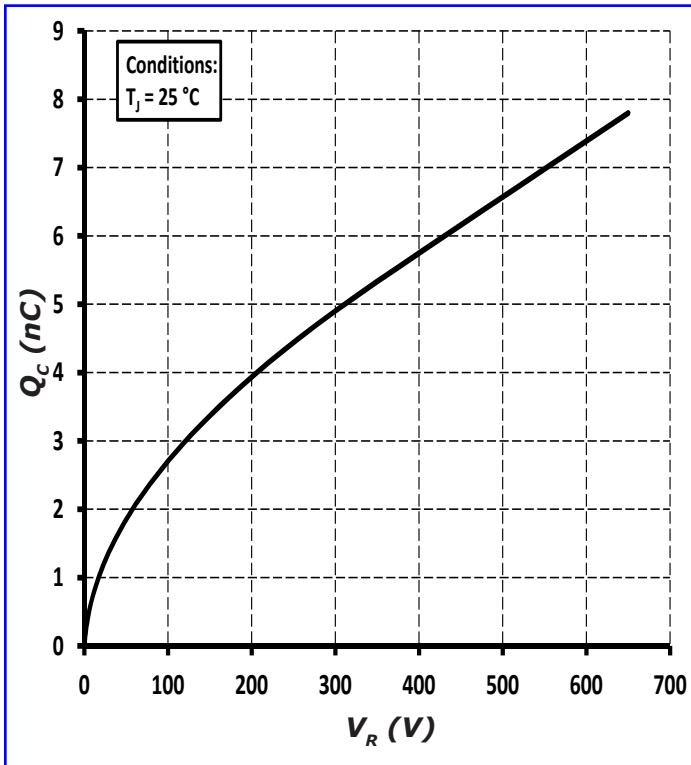


Figure 5. Total Capacitance Charge vs. Reverse Voltage

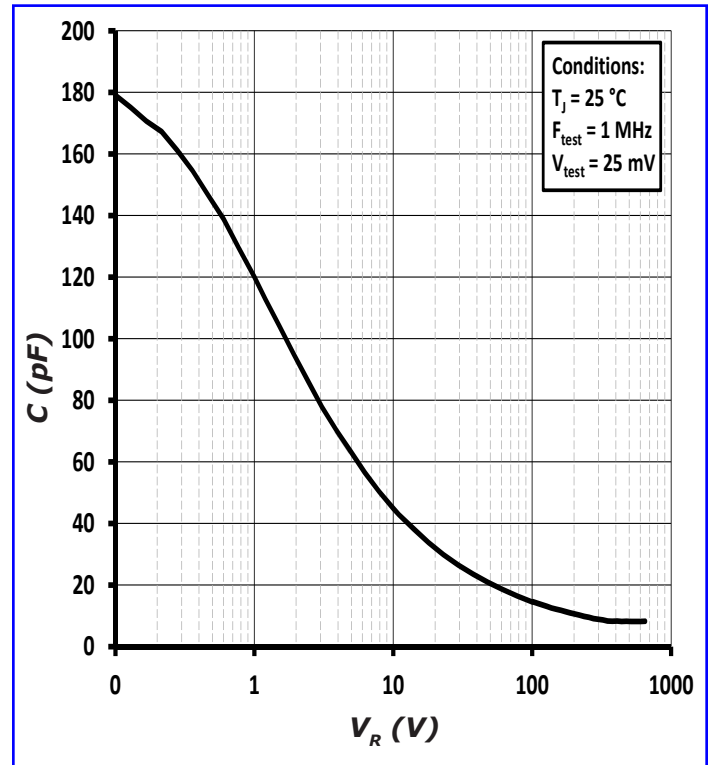


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

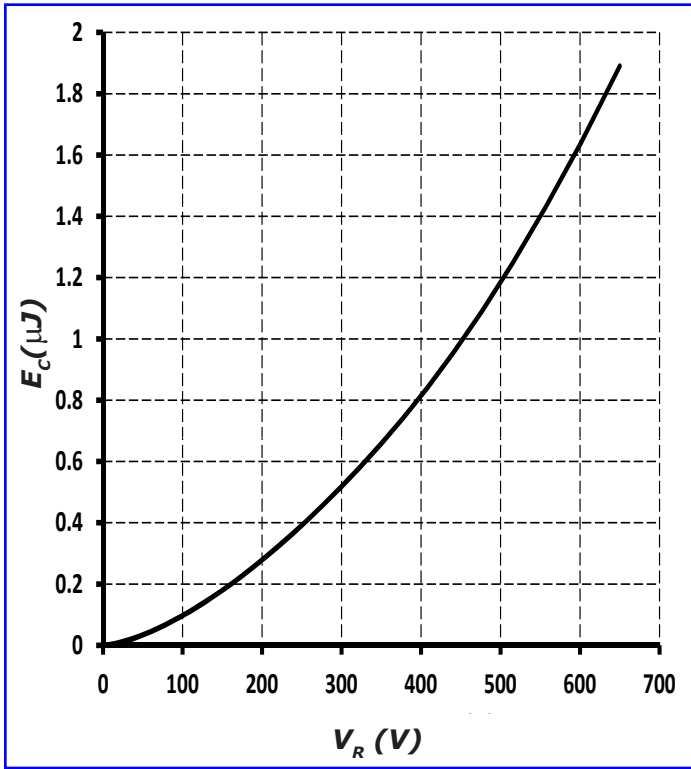


Figure 7. Capacitance Stored Energy

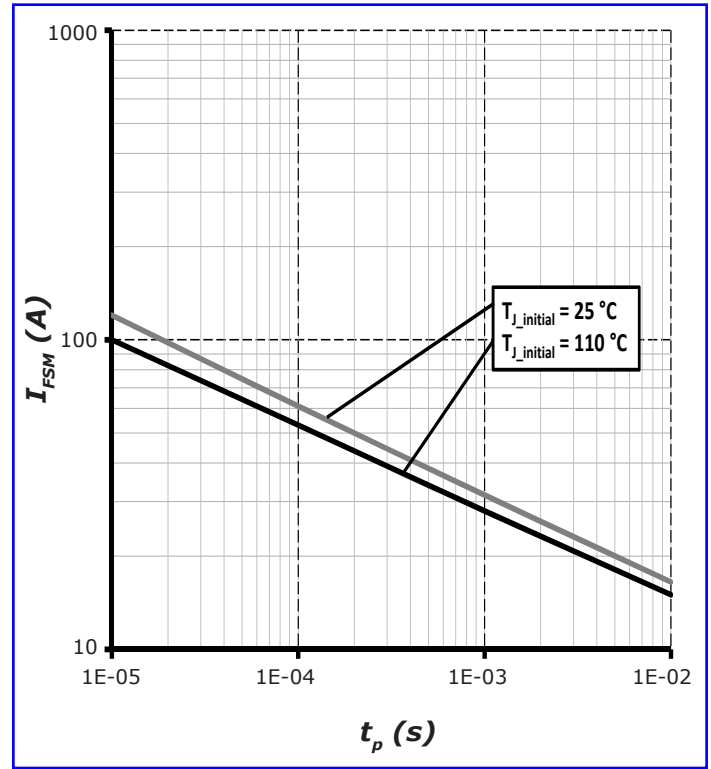


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

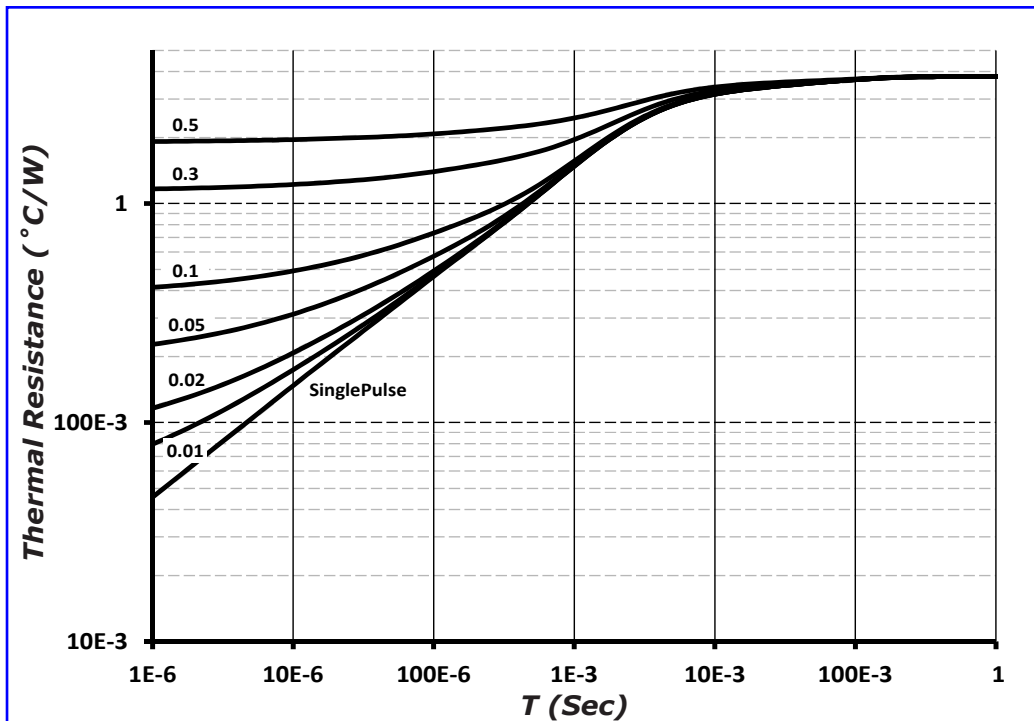
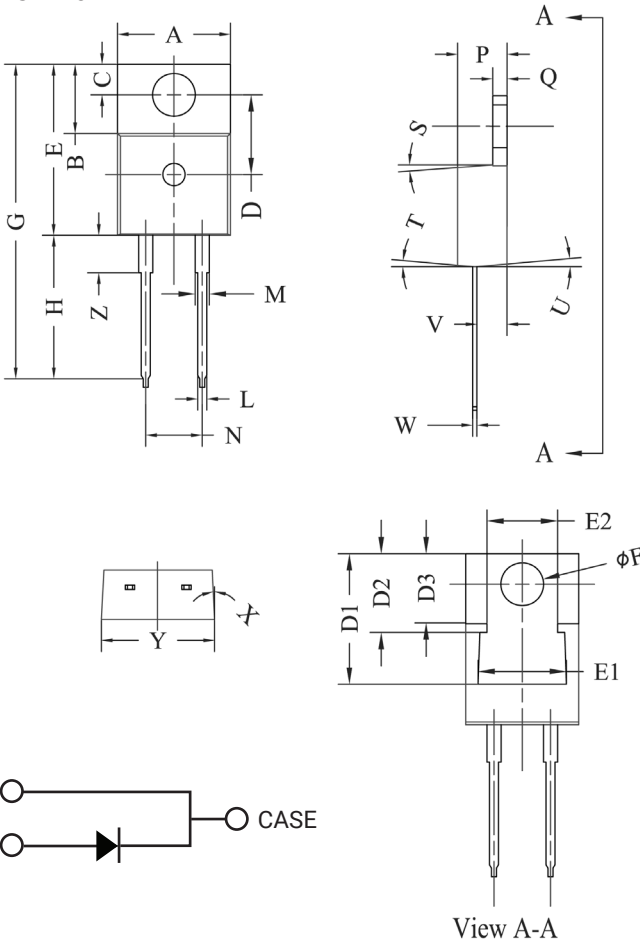


Figure 9. Transient Thermal Impedance

Package Dimensions

Package TO-220-2

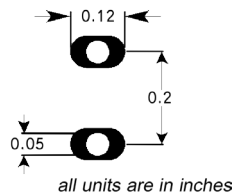


POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.381	.410	9.677	10.414
B	.235	.255	5.969	6.477
C	.100	.120	2.540	3.048
D	.223	.337	5.664	8.560
D1	.457-.490		11.60-12.45 typ	
D2	.277-.303 typ		7.04-7.70 typ	
D3	.244-.252 typ		6.22-6.4 typ	
E	.590	.615	14.986	15.621
E1	.302	.326	7.68	8.28
E2	.227	.251	5.77	6.37
F	.143	.153	3.632	3.886
G	1.105	1.147	28.067	29.134
H	.500	.550	12.700	13.970
L	.025	.036	.635	.914
M	.045	.055	1.143	1.550
N	.195	.205	4.953	5.207
P	.165	.185	4.191	4.699
Q	.048	.054	1.219	1.372
S	3°	6°	3°	6°
T	3°	6°	3°	6°
U	3°	6°	3°	6°
V	.094	.110	2.388	2.794
W	.014	.025	.356	.635
X	3°	5.5°	3°	5.5°
Y	.385	.410	9.779	10.414
Z	.130	.150	3.302	3.810

NOTE:

1. Dimension L, M, W apply for Solder Dip Finish

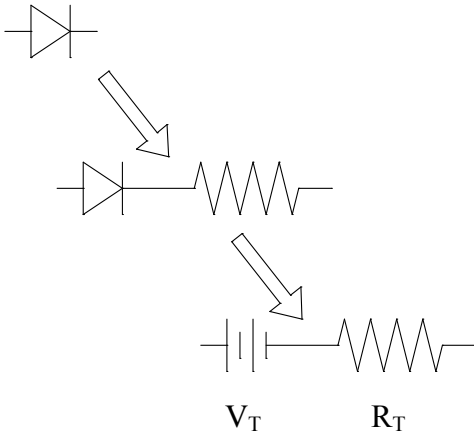
Recommended Solder Pad Layout



TO-220-2

Part Number	Package
GC3D02060A	TO-220-2

Diode Model



$$V_{f_T} = V_T + I_f * R_T$$

$$V_T = 0.98 + (T_j * -1.1 * 10^{-3})$$

$$R_T = 0.18 + (T_j * 1.8 * 10^{-3})$$

Note: T_j = Diode Junction Temperature In Degrees Celsius,
valid from 25°C to 175°C

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Schottky Diodes & Rectifiers](#) category:

Click to view products by [SUPSiC](#) manufacturer:

Other Similar products are found below :

[MA4E2039](#) [MMBD301M3T5G](#) [HFA35HB60C](#) [RB160M-50TR](#) [D83C](#) [BAS16E6433HTMA1](#) [BAS 3010S-02LRH](#) [E6327](#) [BAT 54-02LRH](#)
[E6327](#) [NRVBAF360T3G](#) [NSR05F40QNXT5G](#) [NTE555](#) [JANS1N6640](#) [SS3003CH-TL-E](#) [GA01SHT18](#) [CRS10I30A\(TE85L,QM](#)
[MBRA140TRPBF](#) [MBRB30H30CT-1G](#) [BAT 15-04R](#) [E6152](#) [JANTX1N5712-1](#) [DMJ3940-000](#) [SB007-03C-TB-E](#) [NRVBB20100CTT4G](#)
[NRVBM120LT1G](#) [NTSB30U100CT-1G](#) [CRG04\(T5L,TEMQ\)](#) [ACDBA1100LR-HF](#) [ACDBA1200-HF](#) [ACDBA240-HF](#) [ACDBA3100-HF](#)
[CDBQC0530L-HF](#) [ACDBA260LR-HF](#) [ACDBA1100-HF](#) [10BQ015-M3/5BT](#) [NRVBM120ET1G](#) [VSSB410S-M3/5BT](#) [1N5819T-G](#)
[PDS1040Q-13](#) [B160BQ-13-F](#) [SDM05U20CSP-7](#) [BAS 70-07](#) [E6433](#) [B140S1F-7](#) [HSM560Je3/TR13](#) [DDB2265-000](#) [ZHCS506QTA](#)
[HSM190Je3/TR13](#) [B330AF-13](#) [ACDBUC0230-HF](#) [SDM1U100S1F-7](#) [MBR10200CTF-G1](#) [CDLL5712](#)